

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	4112	MRAM or (magnetoresist adj semiconductor adj memory)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
2	L2	71310	read/write	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
3	L3	1293	read/write near4 current	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
4	L4	5526	write adj current	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07

	L #	Hits	Search Text	DBs	Time Stamp
5	L5	746	(MRAM or (magnetoresist adj semiconductor adj memory)) and (write adj current)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
6	L6	4788	MRAM or (magnetoresist\$6 near4 memory)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
7	L7	98	(MRAM or (magnetoresist\$6 near4 memory)) and (read/write near4 current)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
8	L8	52942	(multilevel or multi-level or third or fourth) near2 line	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07

	L #	Hits	Search Text	DBs	Time Stamp
9	L9	23811	selection near2 line	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
10	L10	399	(MRAM or (magnetoresist\$6 near4 memory)) and ((multilevel or multi-level or third or fourth) near2 line)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
11	L15	4807	MRAM or (magnetoresist\$6 adj random adj access adj memory) or (magnetoresist\$6 near2 RAM) or (magnetoresist\$6 near4 memory)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
12	L16	787	L15 and L4	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07

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13	L18	2254	(438/622) .CCLS.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
14	L22	855	three adj dimensional adj circuit	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
15	L26	272768	three adj dimensional	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
16	L28	696	magnetic adj ram	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07

	L #	Hits	Search Text	DBs	Time Stamp
17	L11	92	(MRAM or (magnetoresist adj semiconductor adj memory)) and (read/write near4 current)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
18	L19	8	L18 and L15	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
19	L20	3	L14 and L15	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
20	L21	2	("6211559").PN.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07

	L #	Hits	Search Text	DBs	Time Stamp
21	L23	3	L22 and L9	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
22	L29	27	L28 and L9	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
23	L13	117	((MRAM or (magnetoresistive near4 memory)) and ((multilevel or multi-level or third or fourth) near2 line)) and (selection near2 line)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
24	L17	147	L16 and L9	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07

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25	L14	242	(438/620) .CCLS.	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
26	L25	218	L22 and (memory or ROM)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
27	L27	249	L26 and MRAM	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
28	L12	786	(MRAM or (magnetoresist near4 memory)) and (write adj current)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07

	L #	Hits	Search Text	DBs	Time Stamp
29	L24	855	three adj dimensional adj circuit	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:07
30	L30	210	(365/157).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:24
31	L31	909	(365/158).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:24
32	L32	239	(365/130).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:25

	L #	Hits	Search Text	DBs	Time Stamp
33	L33	191	(365/148).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:25
34	L34	1502	30 or 31 or 32 or 33	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:26
35	L35	29	34 and 438/?.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:38
36	L36	1483	(438/3).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:38

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37	L37	675	(438/48) .CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:39
38	L38	39	(438/171) .CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 18:39
39	L39	291	(438/210) .CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/29 19:53